

#### 2 - 6 GHz 30 W GaN Power Amplifier

#### **Product Description**

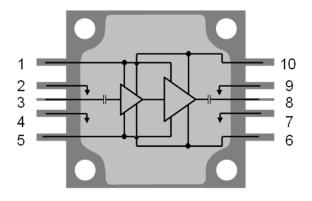
Qorvo's TGA2578-CP is a packaged wideband power amplifier fabricated on Qorvo's QGaN25 0.25um GaN on SiC process. Operating from 2 to 6 GHz, the TGA2578-CP achieves 30 W saturated output power with a power-added efficiency of > 30 %, and > 26 dB small signal gain.

The TGA2578-CP is offered in a 10-lead 15.2 x 15.2 mm bolt-down package. The package has a pure Cu base, offering superior thermal management. The TGA2578-CP is ideally suited to support both commercial and defense applications.

Both RF ports have integrated DC blocking capacitors and are fully matched to 50 Ohms.

Lead-free and RoHS compliant.

## **Functional Block Diagram**





#### **Product Features**

• Frequency Range: 2-6 GHz

• Pout: 45 dBm @ Pin = 23 dBm

• PAE: >30% @ P<sub>IN</sub> = 23 dBm

• Small Signal Gain: > 26 dB

IM3: -30 dBc @ 30 dBm Pout/Tone

• Bias:  $V_D = +28 \text{ V}$ ,  $I_{DQ} = 400 \text{ mA}$ ,  $V_G = -2.8 \text{ V}$  typical

• Package Dimensions: 15.2 x 15.2 x 3.5 mm

Package base is pure Cu offering superior thermal management

Performance is typical across frequency. Please reference electrical specification table and data plots for more details

## **Applications**

- Electronic Warfare
- Radar
- Communications
- Test Instrumentation
- EMC Amplifier

# **Ordering Information**

| Part No.   | Description                        |
|------------|------------------------------------|
| TGA2578-CP | 2 – 6 GHz 30 W GaN Power Amplifier |
| 1096052    | TGA2578-CP Evaluation Board        |



#### 2 - 6 GHz 30 W GaN Power Amplifier

#### **Absolute Maximum Ratings**

| Parameter  | Value / Range                          |
|--|--|
| Drain Voltage (V <sub>D</sub> )  | 40 V                                   |
| Gate Voltage Range (V <sub>G</sub> )                                     | –8 to 0 V                              |
| Drain Current (I <sub>D</sub> )  | 5 A                                    |
| Gate Current (I <sub>G</sub> )   | See plot page 8                        |
| Power Dissipation (PDISS), 85°C  | 85 W                                   |
| Input Power (P <sub>IN</sub> ), 50Ω, 85°C, CW                            | 27 dBm                                 |
| Input Power (P <sub>IN</sub> ), 85°C, VSWR 3:1, V <sub>D</sub> = 28V, CW | 27 dBm                                 |
| Input Power ( $P_{IN}$ ), 85°C, VSWR 10:1, $V_D = 28V$ , CW              | 25 dBm                                 |
| Mounting Temperature   | Refer to<br>Assembly<br>Notes, page 11 |
| Storage Temperature  | –55 to 150 °C                          |

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.

## **Recommended Operating Conditions**

| Parameter                       | Min          | Тур. | Max | Units |
|---------------------------------|--------------|------|-----|-------|
| Drain Voltage (V <sub>D</sub> ) |              | +28  |     | V     |
| Drain Current, (IDQ)            |              | 400  |     | mA    |
| Gate Voltage (V <sub>G</sub> )  | -2.8 Typical |      | V   |       |
| T <sub>BASE</sub> Range         | -40          |      | +85 | ºC    |

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

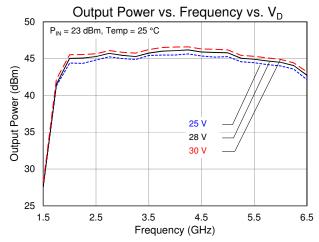
## **Electrical Specifications**

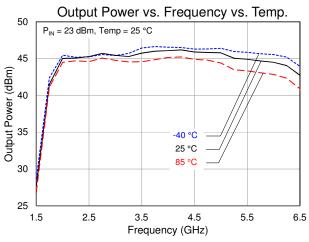
| Parameter   | Min | Тур   | Max | Units  |
|---|-----|-------|-----|--------|
| Operational Frequency Range                         | 2   |       | 6   | GHz    |
| Small Signal Gain                                   |     | >26   |     | dB     |
| Input Return Loss                                   |     | >12   |     | dB     |
| Output Return Loss                                  |     | >5    |     | dB     |
| Output Power (@ P <sub>IN</sub> = 23 dBm)           |     | 45    |     | dBm    |
| Power Added Efficiency (@ P <sub>IN</sub> = 23 dBm) |     | >30   |     | %      |
| IM3 (Pout/tone = 30 dBm/Tone)                       |     | -30   |     | dBc    |
| IM5 (Pout/tone = 30 dBm/Tone)                       |     | -40   |     | dBc    |
| Small Signal Gain Temperature Coefficient           |     | -0.05 |     | dB/°C  |
| Output Power Temperature Coefficient                |     | -0.02 |     | dBm/°C |

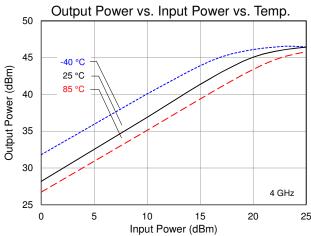
Test conditions unless otherwise noted:  $25\,^{\circ}$ C,  $V_D = +28\,V$ ,  $I_{DQ} = 400\,mA$ ,  $V_G = -2.8\,V$  typical, CW.

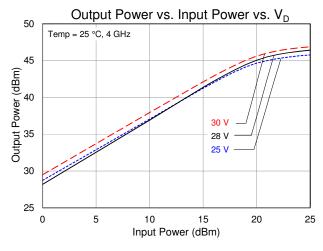


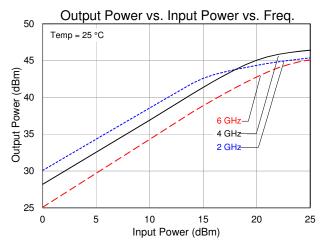
## Typical Performance - Large Signal





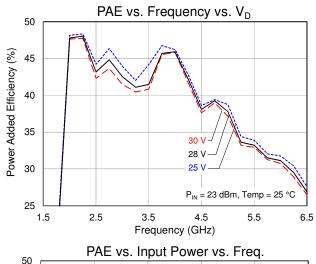


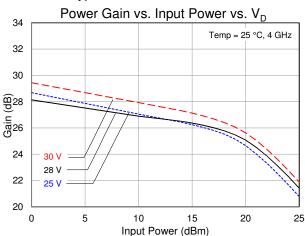


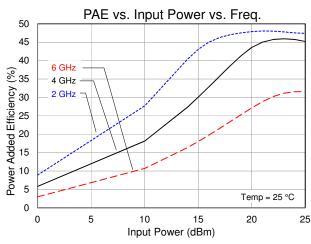


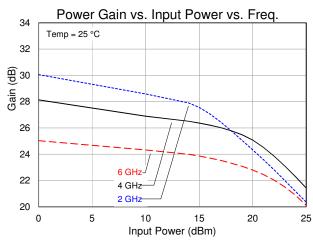


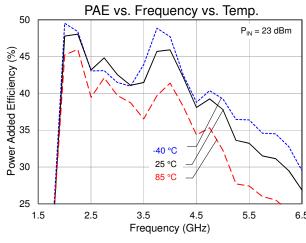
## Typical Performance - Large Signal

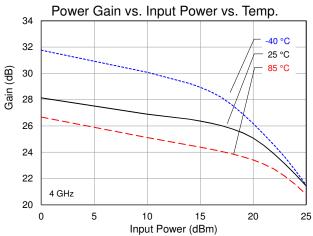






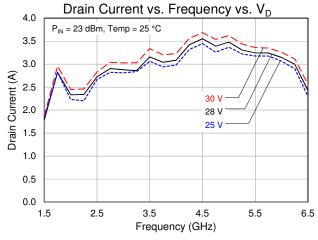


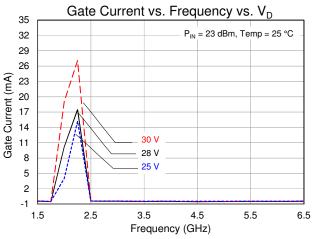


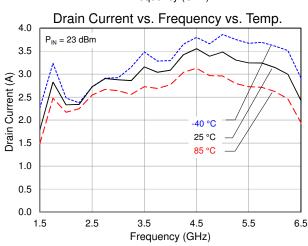


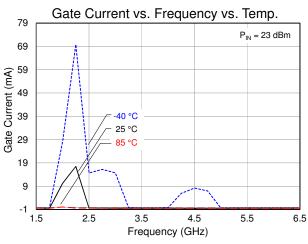


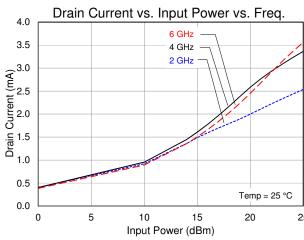
#### Typical Performance - Large Signal

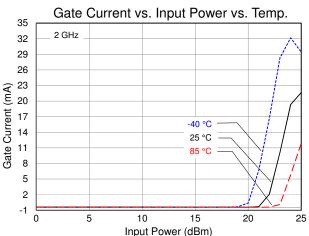










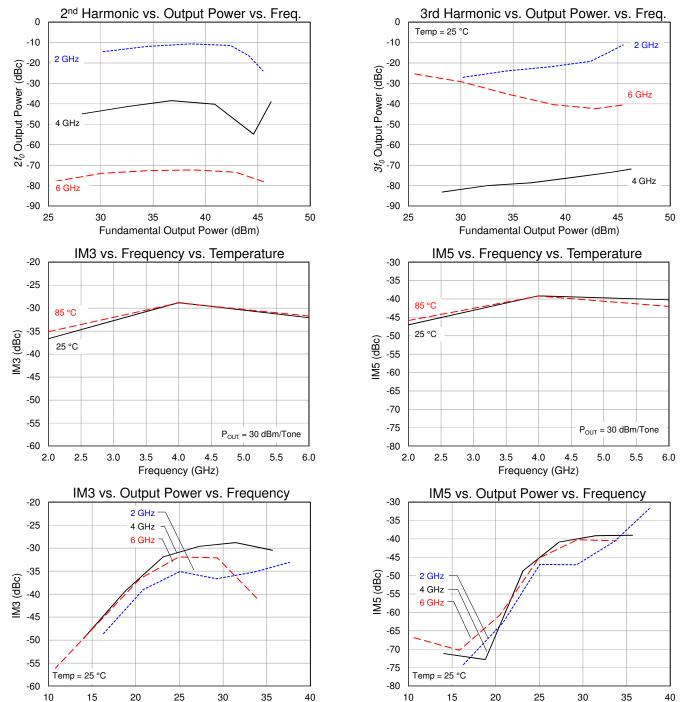




Output Power per Tone (dBm)

## **Typical Performance – Linearity**

Conditions unless otherwise specified:  $V_D = 28 \text{ V}$ ,  $I_{DQ} = 400 \text{ mA}$ ,  $V_G = -2.8 \text{ V}$  Typical, CW.

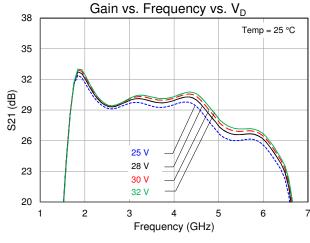


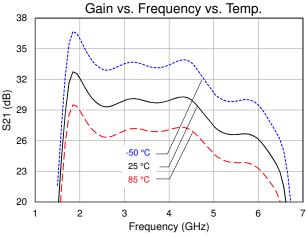
Output Power per Tone (dBm)

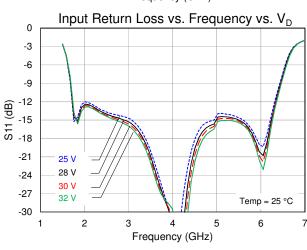


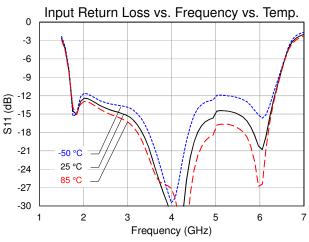
## 2 - 6 GHz 30 W GaN Power Amplifier

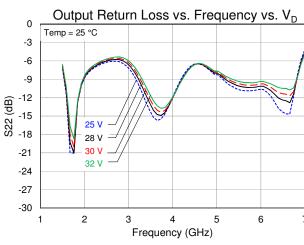
# Performance Plots – Small Signal (CW)

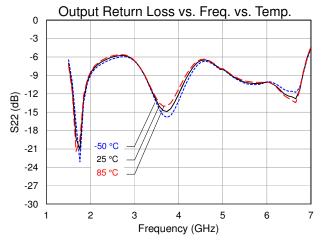












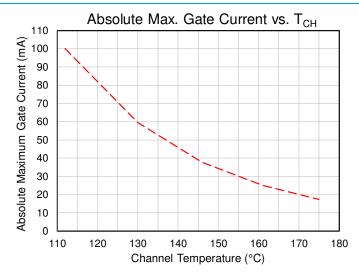
## **Thermal and Reliability Information**

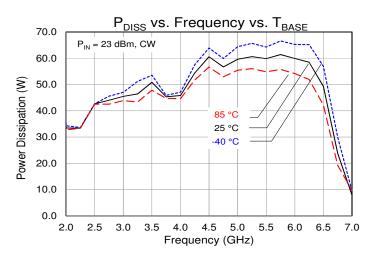
| Parameter  | Test Conditions   | Value | Units |
|--|---|-------|-------|
| Thermal Resistance (θ <sub>JC</sub> ) <sup>(1)</sup> | V <sub>D</sub> = 28 V, I <sub>DQ</sub> = 400 mA, Freq. = 5 GHz  | 1.29  | ºC/W  |
| Channel Temperature, T <sub>CH</sub> (Under RF) (2)  | $T_{base} = 85  ^{\circ}\text{C},  V_D = 28  \text{V},  I_{D\_Drive} = 3  \text{A}, \\ P_{IN} = 23  dBm,  P_{OUT} = 44 dBm,  P_{DISS} = 55  \text{W}$ | 156   | ōС    |

#### Notes:

- 1. Thermal resistance is referenced to the back of package (85 °C)
- 2. Refer to the following document: GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates

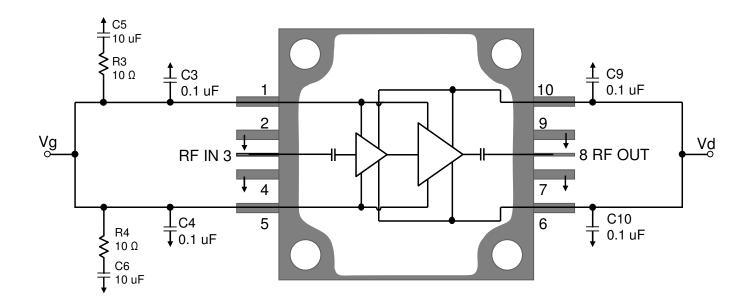
#### **Dissipated Power and Maximum Gate Current**







#### **Applications Information and Pin Layout**



#### Notes:

- 1. V<sub>G</sub> must be biased from both sides (Pins 1 and 5)
- 2. V<sub>D</sub> must be biased from both sides (Pins 6 and 10)

#### **Bias Up Procedure**

| 1. Set I <sub>D</sub> limit to 5 A, I <sub>G</sub> limit to 25 mA        |  |  |
|--|--|--|
| 2. Apply –5 V to V <sub>G</sub>  |  |  |
| 3. Apply 28 V to V <sub>D</sub> ; ensure I <sub>DQ</sub> is approx. 0 mA |  |  |

- 4. Adjust  $V_G$  until  $I_{DQ}$  = 400 mA ( $V_G \sim -2.8 \text{ V Typ.}$ ).
- 5. Turn on RF supply

#### **Bias Down Procedure**

| 1. Turn off RF | supply |
|----------------|--------|
|----------------|--------|

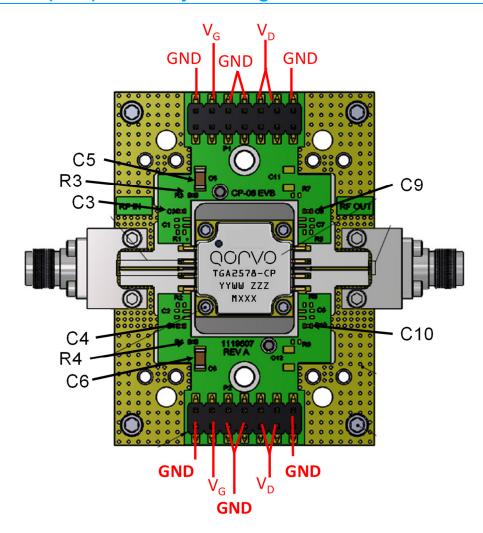
- 2. Reduce  $V_G$  to -5 V; ensure  $I_{DQ}$  is approx. 0 mA
- 3. Set V<sub>D</sub> to 0 V
- 4. Turn off V<sub>D</sub> supply
- 5. Turn off V<sub>G</sub> supply

### **Pin Description**

| Pad No. | Symbol         | Description   |
|---------|----------------|---|
| 1,5     | V <sub>G</sub> | Gate Voltage; Bias network is required; must be biased from both sides; see recommended Application Information above.  |
| 2,4,7,9 | GND            | Must be grounded on the PCB.  |
| 3       | RFIN           | Input; matched to 50 Ω; DC blocked  |
| 6,10    | V <sub>D</sub> | Drain voltage; Bias network is required; must be biased from both sides; see recommended Application Information above. |
| 8       | RFout          | Output; matched to 50 Ω; DC blocked.  |

## 2 - 6 GHz 30 W GaN Power Amplifier

## **Evaluation Board (EVB) Assembly Drawing**



#### PCB NOTES:

- 1. PCB is made from Rogers 4003C dielectric, 0.008 inch thick, 0.5 oz. copper both sides.
- 2. Both Top and Bottom  $V_D$  and  $V_G$  must be biased.

#### **Bill of Materials**

| Reference Des.  | Value  | Description               | Manuf.  | Part Number |
|-----------------|--------|---------------------------|---------|-------------|
| C3, C4, C9, C10 | 0.1 µF | Cap, 0402, 50 V, 10%, X7R | Various | _           |
| C5, C6          | 10 uF  | Cap, 1206, 50 V, 20%, X5R | Various | _           |
| R3, R4          | 10 Ω   | Res, 0402, 5%             | Various | _           |



### **Assembly Notes**

- 1. Carefully clean the PC board, base plate, and package leads with alcohol. Allow it to dry fully.
- 2. To improve the thermal and RF performance, Qorvo recommends attaching a heat sink to the bottom of the package and apply either a thermal compound (Arctic Silver 5 recommended) or a .004 inch (maximum thickness) Indium shim between the heat sink and the package. Refer to the applications note <u>Application of Arctic Silver 5 Thermal Compound and Indium Shims for Qorvo CP-style Packaged Components for more information.</u>
- 3. The component leads should be manually soldered. Apply a low residue solder alloy meeting J-STD-001 (ROL0, ROL1 or equivalent) with a liquidus temperature below 220 °C to each pin of the TGA/QPA/QPMxxxx. The use of low residue/no-clean flux (ROL0, ROL1) is recommended. The package lead temperature should not exceed 260 deg C. Each solder connection should be completed within 2 to 5 seconds. Adding flux during hand soldering of the component leads with localized spot cleaning is acceptable. Soldering irons meeting the requirements of J-STD-001, Appendix A are acceptable.
- 4. The leads should be soldered in a staggered or star pattern from side to side, and never solder two adjacent leads. This allows the heat to dissipate on each lead, and not cause the adjacent leads to become de-soldered and damaged or displaced.



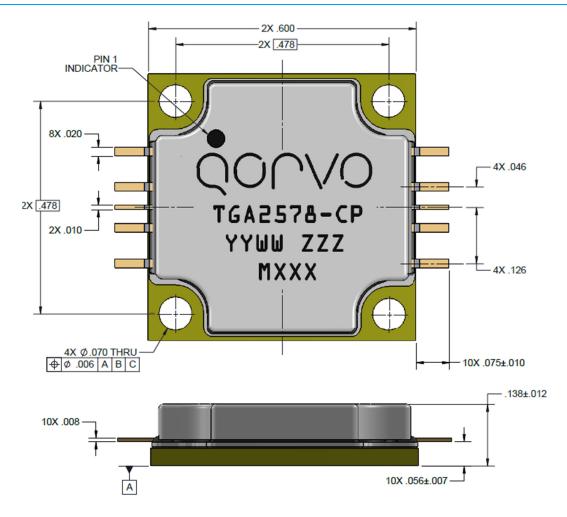
- 5. The packaged part should not be subjected to conventional SMT automated solder reflow processes.
- 6. (The following is for information only. There are many variables in a second level assembly that Qorvo does not control, so Qorvo does not recommend an absolute torque value.) Use screws to attach the component to the heat sink. A suggested final torque value is 16 in-oz. for a 0-80 screw. Start with screws finger tight, then torque to 8 in-oz., then torque to final value. Use the following tightening pattern:







#### **Mechanical Information**



Units: inches

Tolerances: (unless specified)

 $x.xx = \pm 0.01$   $x.xxx = \pm 0.005$ Materials: Base: Copper Leads: Alloy 194 Lid: Plastic

All metalized features are gold plated

Part is epoxy sealed

Marking:

TGA2578-CP: Part number

YY: Part Assembly year WW: Part Assembly week

ZZZ: Serial Number (unique for all parts within one assembly lot)

MXXX: Batch ID



### 2 - 6 GHz 30 W GaN Power Amplifier

#### **Handling Precautions**

| Parameter                      | Rating   | Standard                    |
|--------------------------------|----------|-----------------------------|
| ESD-Human Body Model (HBM)     | Class 1B | JEDEC Standard JESD22 A114  |
| ESD-Charge Device Model (CDM)  | Class C1 | JEDEC Standard JESD22-C101F |
| MSL-Moisture Sensitivity Level | N/A      |                             |



#### **Solderability**

The component leads should be manually soldered, and the package cannot be subjected to conventional reflow processes. The use of no-clean solder to avoid washing after soldering is recommended.

#### **RoHS Compliance**

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU. This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>O<sub>2</sub>) Free
- PFOS Free
- SVHC Free

#### Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: <u>www.qorvo.com</u>
Tel: 1-844-890-8163

Email: customer.support@qorvo.com

## **Important Notice**

The information contained herein is believed to be reliable; however, Qorvo makes no warranties regarding the information contained herein and assumes no responsibility or liability whatsoever for the use of the information contained herein. All information contained herein is subject to change without notice. Customers should obtain and verify the latest relevant information before placing orders for Qorvo products. The information contained herein or any use of such information does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other intellectual property rights, whether with regard to such information itself or anything described by such information. THIS INFORMATION DOES NOT CONSTITUTE A WARRANTY WITH RESPECT TO THE PRODUCTS DESCRIBED HEREIN, AND QORVO HEREBY DISCLAIMS ANY AND ALL WARRANTIES WITH RESPECT TO SUCH PRODUCTS WHETHER EXPRESS OR IMPLIED BY LAW, COURSE OF DEALING, COURSE OF PERFORMANCE, USAGE OF TRADE OR OTHERWISE, INCLUDING THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE.

Without limiting the generality of the foregoing, Qorvo products are not warranted or authorized for use as critical components in medical, life-saving, or life-sustaining applications, or other applications where a failure would reasonably be expected to cause severe personal injury or death.

Copyright 2024 © Qorvo, Inc. | Qorvo is a registered trademark of Qorvo, Inc.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Qorvo:

TGA2578-CP